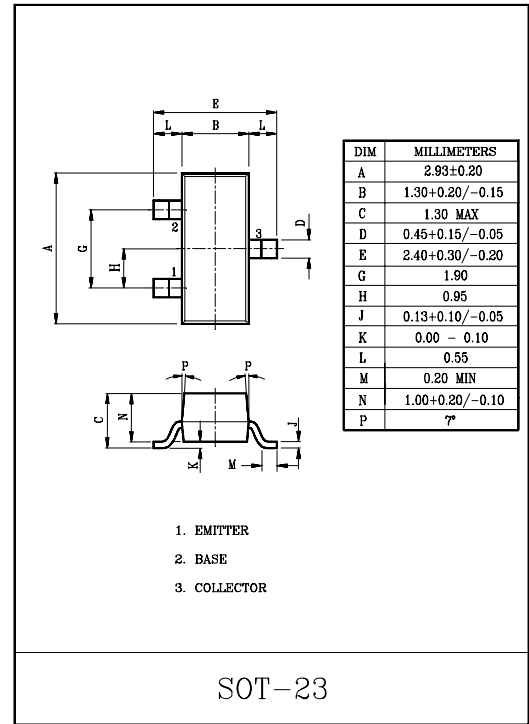


HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

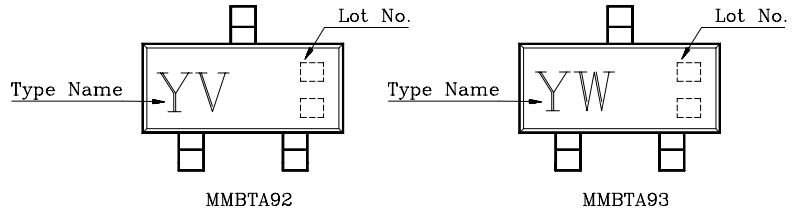
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	MMBTA92	V _{CBO}	-300	V
	MMBTA93		-200	
Collector-Emitter Voltage	MMBTA92	V _{CEO}	-300	V
	MMBTA93		-200	
Emitter-Base Voltage		V _{EBO}	-5.0	V
Collector Current		I _C	-500	mA
Emitter Current		I _E	500	mA
Collector Power Dissipation		P _C *	350	mW
Junction Temperature		T _j	150	°C
Storage Temperature		T _{stg}	-55~150	°C

P_C * : Package mounted on 99.5% alumina 10×8×0.6mm.



Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	MMBTA92	V _{(BR)CBO}	I _C =-100μA, I _E =0	-300	-	-	V
	MMBTA93			-200	-	-	
Collector-Emitter Breakdown Voltage	MMBTA92	V _{(BE)CEO}	I _C =-1.0mA, I _B =0	-300	-	-	V
	MMBTA93			-200	-	-	
DC Current Gain		* h _{FE}	I _C =-1.0mA, V _{CE} =-10V	25	-	-	
			I _C =-10mA, V _{CE} =-10V	40	-	-	
			I _C =-30mA, V _{CE} =-10V	25	-	-	
Collector-Emitter Saturation Voltage		* V _{CE(sat)}	I _C =-20mA, I _B =-2.0mA	-	-	-0.5	V
Base-Emitter Saturation Voltage		* V _{BE(sat)}	I _C =-20mA, I _B =-2.0mA	-	-	-0.9	V
Transition Frequency		f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	50	-	-	MHz
Collector Output Capacitance	MMBTA92	C _{ob}	V _{CB} =-20V, I _E =0, f=1MHz	-	-	6.0	pF
	MMBTA93			-	-	8.0	

*Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2.0%

MMBTA92/93

